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#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	37
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 10x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f100c4t6b

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

## 2.2 Overview

# 2.2.1 ARM<sup>®</sup> Cortex<sup>®</sup>-M3 core with embedded Flash and SRAM

The ARM<sup>®</sup> Cortex<sup>®</sup>-M3 processor is the latest generation of ARM processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM Cortex<sup>®</sup>-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

The STM32F100xx value line family having an embedded ARM core, is therefore compatible with all ARM tools and software.

### 2.2.2 Embedded Flash memory

Up to 128 Kbytes of embedded Flash memory is available for storing programs and data.

#### 2.2.3 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

#### 2.2.4 Embedded SRAM

Up to 8 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states.

#### 2.2.5 Nested vectored interrupt controller (NVIC)

The STM32F100xx value line embeds a nested vectored interrupt controller able to handle up to 41 maskable interrupt channels (not including the 16 interrupt lines of  $Cortex^{\mbox{\ensuremath{\mathbb{R}}}}$ -M3) and 16 priority levels.

- Closely coupled NVIC gives low latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of *late arriving* higher priority interrupts
- Support for tail-chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.

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#### 2.2.18 Serial peripheral interface (SPI)

Up to two SPIs are able to communicate up to 12 Mbit/s in slave and master modes in fullduplex and simplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits.

Both SPIs can be served by the DMA controller.

# 2.2.19 HDMI (high-definition multimedia interface) consumer electronics control (CEC)

The STM32F100xx value line embeds a HDMI-CEC controller that provides hardware support of consumer electronics control (CEC) (Appendix supplement 1 to the HDMI standard).

This protocol provides high-level control functions between all audiovisual products in an environment. It is specified to operate at low speeds with minimum processing and memory overhead.

#### 2.2.20 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high current capable.

The I/Os alternate function configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.

#### 2.2.21 Remap capability

This feature allows the use of a maximum number of peripherals in a given application. Indeed, alternate functions are available not only on the default pins but also on other specific pins onto which they are remappable. This has the advantage of making board design and port usage much more flexible.

For details refer to *Table 4: Low & medium-density STM32F100xx pin definitions*; it shows the list of remappable alternate functions and the pins onto which they can be remapped. See the STM32F10xxx reference manual for software considerations.

#### 2.2.22 ADC (analog-to-digital converter)

The 12-bit analog to digital converter has up to 16 external channels and performs conversions in single-shot or scan modes. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADC can be served by the DMA controller.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.



#### 2.2.23 DAC (digital-to-analog converter)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs. The chosen design structure is composed of integrated resistor strings and an amplifier in noninverting configuration.

This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- up to 10-bit output
- left or right data alignment in 12-bit mode
- synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channels' independent or simultaneous conversions
- DMA capability for each channel
- external triggers for conversion
- input voltage reference V<sub>REF+</sub>

Eight DAC trigger inputs are used in the STM32F100xx. The DAC channels are triggered through the timer update outputs that are also connected to different DMA channels.

#### 2.2.24 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 2 V <  $V_{DDA}$  < 3.6 V. The temperature sensor is internally connected to the ADC1\_IN16 input channel which is used to convert the sensor output voltage into a digital value.

#### 2.2.25 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP Interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG TMS and TCK pins are shared respectively with SWDIO and SWCLK and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.





Figure 4. STM32F100xx value line LQFP64 pinout

#### Figure 5. STM32F100xx value line LQFP48 pinout





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	1	2	3	4	5	6	7	8
A	• /PC14-, 0\\$C32_l'N	, PC13-, TAMPER-RT	(PB9)	( PB4 )	(PB3)	(PA15)	(PA14)	(PA13)
В	, PC15-, OSC32_OU	T (VBAT)	(PB8)	воото	(PD2)	(PC11)	(PC10)	(PA12)
С	OSC_IN	Vss_4	( PB7 )	( PB5 )	(PC12)	(PA10)	( PA9 )	(PA11)
D	OSC_OUT	VDD_4	( PB6 )	(Vss_3)	,VSS_2;	,VSS_1,	( PA8 )	(PC9)
E	(NRST)	(PC1)	( PC0 )	'VDD_3'	'V <sub>DD_2</sub> '	,V <sub>DD_1</sub> ,	( PC7 )	(PC8)
F	(VSSA)	(PC2)	( PA2 )	( PA5 )	(PB0)	(PC6)	(PB15)	(PB14)
G	WREF+	PÁO-WKŲP	( PA3 )	( PA6 )	// PB1 /	( PB2 )	(PB10)	(PB13)
Н	VDDA,	(PA1)	( PA4 )	(PA7)	(PC4)	(PC5)	(PB11)	(PB12)
								Al15

Figure 6. STM32F100xx value line TFBGA64 ballout

Table 4. Low & medium-density STM32F100xx pin definitions

	Pi	ns				2)		Alternate functions <sup>(3)(4)</sup>		
LQFP100	LQFP64	TFBGA64	LQFP48	Pin name	Type <sup>(1)</sup>	I / O level <sub>(</sub>	Main function <sup>(3)</sup> (after reset) Default		Remap	
1	-	-	-	PE2	I/O	FT	PE2	TRACECLK	-	
2	-	-	-	PE3	I/O	FT	PE3	TRACED0	-	
3	-	-	-	PE4	I/O	FT	PE4	TRACED1	-	
4	-	-	-	PE5	I/O	FT	PE5	TRACED2	-	
5	-	-	-	PE6	I/O	FT	PE6	TRACED3	-	
6	1	B2	1	V <sub>BAT</sub>	S	-	V <sub>BAT</sub>	-	-	
7	2	A2	2	PC13-TAMPER-RTC <sup>(5)</sup>	I/O	-	PC13 <sup>(6)</sup>	TAMPER-RTC	-	
8	3	A1	3	PC14-OSC32_IN <sup>(5)</sup>	I/O	-	PC14 <sup>(6)</sup>	OSC32_IN	-	



1. I = input, O = output, S = supply, HiZ= high impedance.

- Function availability depends on the chosen device. For devices having reduced peripheral counts, it is always the lower number of peripherals that is included. For example, if a device has only one SPI, two USARTs and two timers, they will be called SPI1, USART1 & USART2 and TIM2 & TIM 3, respectively. Refer to Table 2 on page 11.
- 4. If several peripherals share the same I/O pin, to avoid conflict between these alternate functions only one peripheral should be enabled at a time through the peripheral clock enable bit (in the corresponding RCC peripheral clock enable register).
- PC13, PC14 and PC15 are supplied through the power switch and since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is restricted: the speed should not exceed 2 MHz with a maximum load of 30 pF and these IOs must *not* be used as a current source (e.g. to drive an LED).
- 6. Main function after the first backup domain power-up. Later on, it depends on the contents of the Backup registers even after reset (because these registers are not reset by the main reset). For details on how to manage these IOs, refer to the Battery backup domain and BKP register description sections in the STM32F10xxx reference manual, available from the STMicroelectronics website: www.st.com.
- 7. The pins number 2 and 3 in the VFQFPN36 package, 5 and 6 in the LQFP48 and LQFP64 packages and C1 and C2 in the TFBGA64 package are configured as OSC\_IN/OSC\_OUT after reset, however the functionality of PD0 and PD1 can be remapped by software on these pins. For more details, refer to the Alternate function I/O and debug configuration section in the STM32F10xxx reference manual.
- 8. Unlike in the LQFP64 package, there is no PC3 in the TFBGA64 package. The V<sub>REF+</sub> functionality is provided instead.
- 9. I2C2 is not present on low-density value line devices.
- 10. SPI2 is not present on low-density value line devices.
- 11. TIM4 is not present on low-density value line devices.
- 12. This alternate function can be remapped by software to some other port pins (if available on the used package). For more details, refer to the Alternate function I/O and debug configuration section in the STM32F10xxx reference manual, available from the STMicroelectronics website: www.st.com.



<sup>2.</sup> FT= 5 V tolerant.

#### 5.3.4 Embedded reference voltage

The parameters given in *Table 11* are derived from tests performed under the ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 8*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>REFINT</sub>	Internal reference voltage	–40 °C < T <sub>A</sub> < +105 °C	1.16	1.20	1.26	V
		–40 °C < T <sub>A</sub> < +85 °C	1.16	1.20	1.24	V
T <sub>S_vrefint</sub> <sup>(1)</sup>	ADC sampling time when reading the internal reference voltage	-	-	5.1	17.1 <sup>(2)</sup>	μs
V <sub>RERINT</sub> <sup>(2)</sup>	Internal reference voltage spread over the temperature range	V <sub>DD</sub> = 3 V ±10 mV	-	-	10	mV
T <sub>Coeff</sub> <sup>(2)</sup>	Temperature coefficient	-	-	-	100	ppm/°C

Table 11. Embedded internal reference voltage

1. Shortest sampling time can be determined in the application by multiple iterations.

2. Guaranteed by design.

### 5.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 11: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code.

#### Maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V<sub>DD</sub> or V<sub>SS</sub> (no load)
- All peripherals are disabled except if it is explicitly mentioned
- Prefetch in on (reminder: this bit must be set before clock setting and bus prescaling)
- When the peripherals are enabled f<sub>PCLK1</sub> = f<sub>HCLK</sub>/2, f<sub>PCLK2</sub> = f<sub>HCLK</sub>

The parameters given in *Table 12* are derived from tests performed under the ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 8*.





Figure 15. Typical current consumption in Stop mode with regulator in Run mode versus temperature at  $V_{DD}$  = 3.3 V and 3.6 V







#### Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 22*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Note: For  $C_{L1}$  and  $C_{L2}$  it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator.  $C_{L1}$  and  $C_{L2}$  are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of  $C_{L1}$  and  $C_{L2}$ .

Load capacitance  $C_L$  has the following formula:  $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$  where  $C_{stray}$  is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

For further details, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

**Caution:** To avoid exceeding the maximum value of  $C_{L1}$  and  $C_{L2}$  (15 pF) it is strongly recommended to use a resonator with a load capacitance  $C_L \le 7$  pF. Never use a resonator with a load capacitance of 12.5 pF.

**Example:** if you choose a resonator with a load capacitance of  $C_L$  = 6 pF, and  $C_{stray}$  = 2 pF, then  $C_{L1}$  =  $C_{L2}$  = 8 pF.

Symbol	Parameter	Conditions		Min	Тур	Max       -       15       1.4       -       5       -  - -	Unit
R <sub>F</sub>	Feedback resistor		-	-	5	-	MΩ
C <sub>L1</sub> C <sub>L2</sub> <sup>(2)</sup>	Recommended load capacitance versus equivalent serial resistance of the crystal $(R_S)^{(3)}$	R <sub>S</sub> = 30 KΩ		-	-	15	pF
l <sub>2</sub>	LSE driving current	V <sub>DD</sub> = 3	.3 V V <sub>IN</sub> = V <sub>SS</sub>	-	-	1.4	μA
9 <sub>m</sub>	Oscillator transconductance		5	-	-	μA/V	
	Charlus time		T <sub>A</sub> = 50 °C	-	1.5	-	- S
		V <sub>nn</sub> is	T <sub>A</sub> = 25 °C	-	2.5	-	
			T <sub>A</sub> = 10 °C	-	4	-	
+ (4)			T <sub>A</sub> = 0 °C	-	6	-	
'SU(LSE)`´		stabilized	T <sub>A</sub> = -10 °C	-	10	-	
			T <sub>A</sub> = -20 °C	-	17	-	
			T <sub>A</sub> = -30 °C	-	32	-	
			T <sub>A</sub> = -40 °C	-	60	-	

Table 22. LSE oscillator characteristics  $(f_{LSE} = 32.768 \text{ kHz})^{(1)}$ 

1. Guaranteed by characterization results.

2. Refer to the note and caution paragraphs above the table.

- The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R<sub>S</sub> value for example MSIV-TIN32.768 kHz. Refer to crystal manufacturer for more details
- 4. t<sub>SU(LSE)</sub> is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer



#### **Electromagnetic Interference (EMI)**

The electromagnetic field emitted by the device is monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Symbol	Parameter	Conditions	Monitored	Max vs. [f <sub>HSE</sub> /f <sub>HCLK</sub> ]	Unit	
	i ulullotoi	Conditione	frequency band	8/24 MHz	onic	
		Deals lavel	V <sub>DD</sub> = 3.6 V, T <sub>A</sub> = 25°C, LQFP100 package	0.1 MHz to 30 MHz	9	
	9			30 MHz to 130 MHz	16	dBµV
S <sub>EMI</sub>	reakievei	compliant with SAE J1752/3	130 MHz to 1GHz	19		
			SAE EMI Level	4	-	

Table 30. EMI characteristics
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#### 5.3.11 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

#### Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts  $\times$  (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 31. ESD absolute maximu	um ratings
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Symbol	Ratings	Conditions	Class	Maximum value <sup>(1)</sup>	Unit
V <sub>ESD(HBM)</sub>	Electrostatic discharge voltage (human body model)	$T_A = +25 \ ^{\circ}C$ conforming to JESD22-A114	2	2000	V
V <sub>ESD(CDM)</sub>	Electrostatic discharge voltage (charge device model)	$T_A = +25 \ ^{\circ}C$ conforming to JESD22-C101	111	500	v

1. Based on characterization results, not tested in production.

#### Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD78 IC latch-up standard.

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105$ °C conforming to JESD78	II level A

#### Table 32. Electrical sensitivities





Figure 22. Standard I/O input characteristics - CMOS port







#### Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 26* and *Table 36*, respectively.

Unless otherwise specified, the parameters given in *Table 36* are derived from tests performed under the ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 8*.

MODEx [1:0] bit value <sup>(1)</sup>	Symbol	Parameter	Conditions	Мах	Unit	
	f <sub>max(IO)out</sub>	Maximum frequency <sup>(2)</sup>	$C_L$ = 50 pF, $V_{DD}$ = 2 V to 3.6 V	2 <sup>(3)</sup>	MHz	
10	t <sub>f(IO)out</sub>	Output high to low level fall time		125 <sup>(3)</sup>	20	
	t <sub>r(IO)out</sub>	Output low to high level rise time	$V_{\rm L} = 50  \text{pr},  V_{\rm DD} = 2  \text{V}  10  3.0  \text{V}$	125 <sup>(3)</sup>	ns	
01	f <sub>max(IO)out</sub>	Maximum frequency <sup>(2)</sup>	$C_{L}$ = 50 pF, $V_{DD}$ = 2 V to 3.6 V	10 <sup>(3)</sup>	MHz	
	t <sub>f(IO)out</sub>	Output high to low level fall time		25 <sup>(3)</sup>	20	
	t <sub>r(IO)out</sub>	Output low to high level rise time	CL- 50 μr, VDD - 2 V to 5.6 V	25 <sup>(3)</sup>	115	
	f <sub>max(IO)out</sub>	Maximum frequency <sup>(2)</sup>	$C_{L}$ = 50 pF, $V_{DD}$ = 2 V to 3.6 V	24	MHz	
	t <sub>f(IO)out</sub>			$C_{L}$ = 30 pF, $V_{DD}$ = 2.7 V to 3.6 V	5 <sup>(3)</sup>	
		Output high to low level fall time	$C_{L}$ = 50 pF, $V_{DD}$ = 2.7 V to 3.6 V	8 <sup>(3)</sup>	ns	
11			$C_{L}$ = 50 pF, $V_{DD}$ = 2 V to 2.7 V	12 <sup>(3)</sup>		
			$C_{L}$ = 30 pF, $V_{DD}$ = 2.7 V to 3.6 V	5 <sup>(3)</sup>		
	t <sub>r(IO)out</sub>	Output low to high level rise time	$C_{L}$ = 50 pF, $V_{DD}$ = 2.7 V to 3.6 V	8 <sup>(3)</sup>	1	
			$C_{L}$ = 50 pF, $V_{DD}$ = 2 V to 2.7 V	12 <sup>(3)</sup>		
-	t <sub>EXTIpw</sub>	Pulse width of external signals detected by the EXTI controller	-	10 <sup>(3)</sup>	ns	

1. The I/O speed is configured using the MODEx[1:0] bits. Refer to the STM32F10xxx reference manual for a description of GPIO Port configuration register.

2. The maximum frequency is defined in *Figure 26*.

3. Guaranteed by design.



### 5.3.16 Communications interfaces

#### I<sup>2</sup>C interface characteristics

Unless otherwise specified, the parameters given in *Table 39* are derived from tests performed under the ambient temperature,  $f_{PCLK1}$  frequency and  $V_{DD}$  supply voltage conditions summarized in *Table 8*.

The STM32F100xx value line I<sup>2</sup>C interface meets the requirements of the standard I<sup>2</sup>C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V<sub>DD</sub> is disabled, but is still present.

The I<sup>2</sup>C characteristics are described in *Table 39*. Refer also to *Section 5.3.12: I/O current injection characteristics* for more details on the input/output alternate function characteristics (SDA and SCL).

Symbol	Parameter	Standard n	node l <sup>2</sup> C <sup>(1)</sup>	Fast mode	Unit		
Symbol	Farameter	Min	Max	Min	Мах	0	
t <sub>w(SCLL)</sub>	SCL clock low time	4.7	-	1.3	-	116	
t <sub>w(SCLH)</sub>	SCL clock high time	4.0	-	0.6	-	μο	
t <sub>su(SDA)</sub>	SDA setup time	250	-	100	-		
t <sub>h(SDA)</sub>	SDA data hold time	0	-	0	900 <sup>(3)</sup>		
t <sub>r(SDA)</sub> t <sub>r(SCL)</sub>	SDA and SCL rise time	-	1000	-	300	ns	
t <sub>f(SDA)</sub> t <sub>f(SCL)</sub>	SDA and SCL fall time	-	300	-	300		
t <sub>h(STA)</sub>	Start condition hold time	4.0	-	0.6	-		
t <sub>su(STA)</sub>	Repeated Start condition setup time	4.7	-	0.6	-	μs	
t <sub>su(STO)</sub>	Stop condition setup time	4.0	-	0.6	-	μs	
t <sub>w(STO:STA)</sub>	Stop to Start condition time (bus free)	4.7	-	1.3	-	μs	
Cb	Capacitive load for each bus line	-	400	-	400	pF	

Table 39, IFC characteristic	Table	39.	I <sup>2</sup> C	chara	cteristic
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1. Guaranteed by design.

f<sub>PCLK1</sub> must be at least 2 MHz to achieve standard mode I<sup>2</sup>C frequencies. It must be at least 4 MHz to achieve fast mode I<sup>2</sup>C frequencies. It must be a multiple of 10 MHz to reach the 400 kHz maximum I2C fast mode clock.

3. The maximum Data hold time has only to be met if the interface does not stretch the low period of SCL signal.



T <sub>s</sub> (cycles)	t <sub>S</sub> (μs)	R <sub>AIN</sub> max (kΩ)
1.5	0.125	0.4
7.5	0.625	5.9
13.5	1.125	11.4
28.5	2.375	25.2
41.5	3.45	37.2
55.5	4.625	50
71.5	5.96	NA
239.5	20	NA

#### Table 43. $R_{AIN}$ max for $f_{ADC} = 12 \text{ MHz}^{(1)}$

1. Guaranteed by design.

Symbol	Parameter	Test conditions	Тур	Max	Unit
ET	Total unadjusted error	$f_{PCLK2} = 24 \text{ MHz},$	±1.3	±2.2	
EO	Offset error	$f_{ADC} = 12 \text{ MHz}, R_{AIN} < 10 \text{ k}\Omega$	±1	±1.5	
EG	Gain error	$V_{REF+} = V_{DDA}$	±0.5	±1.5	LSB
ED	Differential linearity error	T <sub>A</sub> = 25 °C	±0.7	±1	
EL	Integral linearity error	Measurements made after ADC calibration	±0.8	±1.5	

1. ADC DC accuracy values are measured after internal calibration.

2. Guaranteed by characterization results.

Table	45.	ADC	accuracy	(1)	(2)	(3)
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Symbol	Parameter	Test conditions	Тур	Мах	Unit
ET	Total unadjusted error	f <sub>PCLK2</sub> = 24 MHz,	±2	±5	
EO	Offset error	$f_{ADC}$ = 12 MHz, $R_{AIN}$ < 10 kΩ	±1.5	±2.5	
EG	Gain error	$V_{DDA} = 2.4 V$ to 3.6 V	±1.5	±3	LSB
ED	Differential linearity error	Measurements made after	±1	±2	
EL	Integral linearity error	ADC calibration	±1.5	±3	

1. ADC DC accuracy values are measured after internal calibration.

2. Better performance could be achieved in restricted  $V_{DD}$ , frequency,  $V_{REF}$  and temperature ranges.

3. Guaranteed by characterization results.

Note:ADC accuracy vs. negative injection current: Injecting a negative current on any analog<br/>input pins should be avoided as this significantly reduces the accuracy of the conversion<br/>being performed on another analog input. It is recommended to add a Schottky diode (pin to<br/>ground) to analog pins which may potentially inject negative currents.<br/>Any positive injection current within the limits specified for I<sub>INJ(PIN)</sub> and ΣI<sub>INJ(PIN)</sub> in<br/>Section 5.3.12 does not affect the ADC accuracy.



# 6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.

## 6.1 LQFP100 package information



#### Figure 37. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline

1. Drawing is not to scale. Dimensions are in millimeters.



#### **Device marking for LQFP100**

The following figure gives an example of topside marking and pin 1 position identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.



#### Figure 39.LQFP100 marking example (package top view)

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



## 6.2 LQFP64 package information

Figure 40.LQFP64 – 10 x 10 mm 64 pin low-profile quad flat package outline



1. Drawing is not in scale.

Table 49. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package
mechanical data

Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Тур	Max	Min	Тур	Max
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
с	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-
E3	-	7.500	-	-	0.2953	-



# Table 50. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ballgrid array package mechanical data

Gumbal	millimeters			inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max
E1	-	3.500	-	-	0.1378	-
е	-	0.500	-	-	0.0197	-
F	-	0.750	-	-	0.0295	-
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

# Figure 44. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array, recommended footprint



#### Table 51. TFBGA64 recommended PCB design rules (0.5 mm pitch BGA) Image: Comparison of the second secon

Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 1.125 mm
Pad trace width	0.100 mm



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#### **Device marking for TFBGA64**

The following figure gives an example of topside marking and pin 1 position identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



Using the values obtained in *Table 53*  $T_{Jmax}$  is calculated as follows:

- For LQFP100, 46 °C/W
- $T_{Jmax}$  = 115 °C + (46 °C/W × 134 mW) = 115 °C + 6.2 °C = 121.2 °C

This is within the range of the suffix 7 version parts (–40 <  $T_J$  < 125 °C).

In this case, parts must be ordered at least with the temperature range suffix 7 (see *Table 54: Ordering information scheme*).





